2018년 2월 7일(수), 13:15-14:45 Room I (청옥II+III, 6층)

K. Memory (Design & Process Technology) 분과 [WI3-K] FeRAM and Transparent ReRAM

WI3-K-1 13:15-13:30	Characterization of Ferroelectric Hafnium Oxide Thin Film Sang Hyun Sung ¹ , Do Hyun Kim ¹ , Il Suk Kang ² , and Keon Jae Lee ¹ ¹ Department of Materials Sciences and Engineering, KAIST, ² Nano Research Division, National NanoFab Center
WI3-K-2 13:30-13:45	New Non-volatile Multi-level Cell Using Epitaxial Strain Effect and Double Ferroelectric Tunnel Junctions Moonhoi Kim, Junbeom Seo, and Mincheol Shin School of Electrical Engineering, KAIST
WI3-K-3 13:45-14:00	Improvement of ZnO Resistive Switching Devices by Metal Thin Layer on ITO Bottom Electrode for Transparent Devices Taehoon Lee ¹ , Yong Chan Jung ¹ , Sejong Seong, ¹ , Seon Yong Kim ¹ , In-Sung Park ^{1,2} , and Jinho Ahn ^{1,2} ¹ Division of Materials Science and Engineering, Hanyang University, ² Institute of Nano Science and Technology, Hanyang University
WI3-K-4 14:00-14:15	Investigation on Resistive Switching in Zn-Sn-O Film Using Microwave Irradiation Tae-Wan Kim and Won-Ju Cho Department of Electronic Materials Engineering, Kwangwoon University
WI3-K-5 14:15-14:30	Analysis of LRS Retention Fail based on Joule Heating Effect in InGaZnO RRAM Geumho Ahn, Jun Tae Jang, Daehyun Ko, Hyeri Yu, Haesun Jung, Jihyun Rhee, Hyun-Sun Mo, Sung-Jin Choi, Dong Myong Kim, and Dae Hwan Kim School of Electrical Engineering, Kookmin University
WI3-K-6 14:30-14:45	Capacitorless 1T-DRAM Device Sehyun Kwon ¹ , Minho Choi ¹ , In-sung Park ² , Yong Tae Kim ³ , and Jinho Ahn ^{1,2} ¹ Department of Materials Science and Engineering, Hanyang University, ² Institute of Nano Science and Technology, Hanyang University, ³ KIST